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Material and Process
Toshio Konishi, Toppan Printing Company, Ltd. (Japan)
Koji Murano, Toshiba Corporation (Japan)
Thomas B. Faure, IBM Corporation (United States)

Process and Repair
Toshio Konishi, Toppan Printing Company, Ltd. (Japan)
Koji Murano, Toshiba Corporation (Japan)
Thomas B. Faure, IBM Corporation (United States)

Pattern Generation
Noriaki Nakayamada, NuFlare Technology, Inc. (Japan)
Jeff Farnsworth, Intel Corporation (United States)

Metrology and Inspection
Tatsuya Tomita, Dai Nippon Printing Company, Ltd. (Japan)
Shinji Akima, Toppan Printing Company, Ltd. (Japan)
Byung Gook Kim, SAMSUNG Electronics Company, Ltd. (Korea, Republic of)

Mask-related Lithography
Minoru Sugawara, Sony Corporation (Japan)
Steffen Schulze, Mentor Graphics Corporation (United States)

EDA, DFM, and MDP
Kokoro Kato, SII NanoTechnology Inc. (Japan)
Nobuyuki Nishiguchi, Semiconductor Technology Academic Research Center (Japan)